



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ $V_{GS} = 5.0V$	350mA
00 V	2.5Ω @ V _{GS} = 2.5V	SSUTIA

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

- Low On-Resistance: RDS(ON)
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

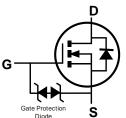
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe.
 Solderable per MIL-STD-202, Method 208(€3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



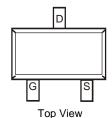


SOT523

Top View







Pin Out Configuration

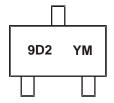
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN61D9UT-7	SOT523	3000/Tape & Reel
DMN61D9UT-13	SOT523	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



9D2 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н	I	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			VDSS	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) Vgs = 5.0V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	l _D	350 280	mA
Maximum Continuous Body Diode Forward Currer	nt (Note 6)	Is	350	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)		IDM	1.1	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	260	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	491	°C/W
Total Power Dissipation (Note 6)		PD	370	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	342	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

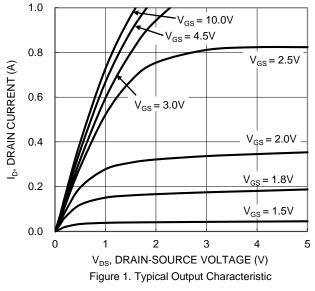
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1.0	μΑ	V _{DS} = 60V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	0.5	_	1.0	V	$V_{DS} = 10V, I_{D} = 250\mu A$	
			1.2	2.0		$V_{GS} = 5.0V, I_{D} = 0.05A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.6	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$	
			2.5	3.5		$V_{GS} = 1.8V, I_{D} = 0.05A$	
Forward Transconductance	Y _{fs}	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage	VsD	_	0.75	1.4	V	V _G S = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		28.5	_	рF	V 00V V 0V	
Output Capacitance	Coss	_	3.9	_	pF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	2.5	_	pF	1 = 1.000112	
Gate Resistance	Rg	_	65	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$	
Total Gate Charge	Qg	_	0.4	_	nC	45)//	
Gate-Source Charge	Qgs	_	0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Qgd	_	0.1	_	nC	I _D = 250mA	
Turn-On Delay Time	tD(ON)	_	2.1	_	ns		
Turn-On Rise Time	tr		1.8	_	ns	V _{DD} = 30V, V _{GS} = 10V,	
Turn-Off Delay Time	tD(OFF)	_	14.4	_	ns	$R_G = 25\Omega$, $I_D = 200mA$	
Turn-Off Fall Time	tF	_	8.4	_	ns		

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





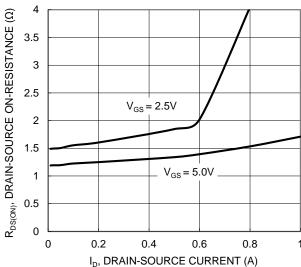


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

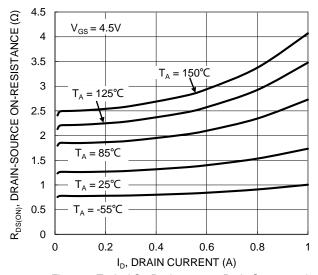


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

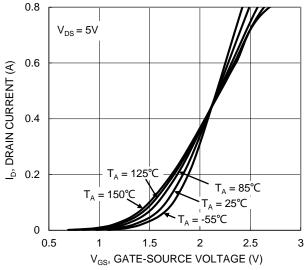


Figure 2. Typical Transfer Characteristic

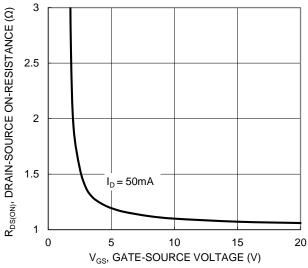


Figure 4. Typical Transfer Characteristic

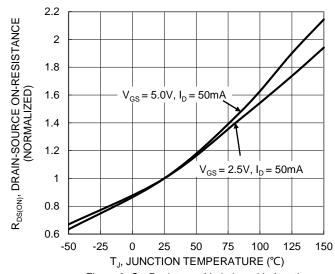


Figure 6. On-Resistance Variation with Junction Temperature



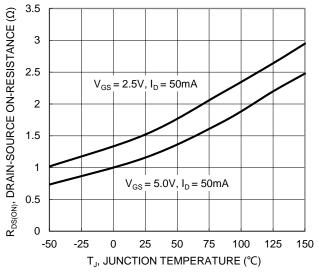
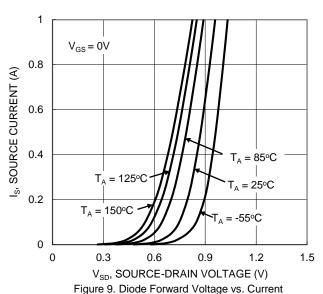


Figure 7. On-Resistance Variation with Junction Temperature



4.5 4 3.5 3 $V_{GS}(V)$ 2.5 2 $V_{DS} = 10V, I_{D} = 250mA$ 1.5 1 0.5 0 0 0.1 0.2 0.3 0.4 0.5 Q_g (nC)

Figure 11. Gate Charge

4 of 7

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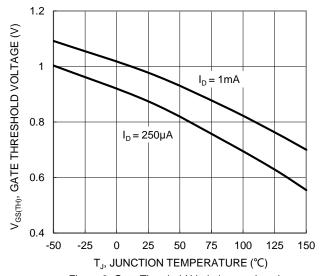


Figure 8. Gate Threshold Variation vs. Junction Temperature

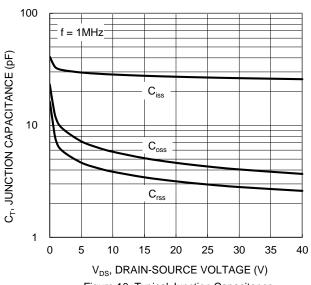
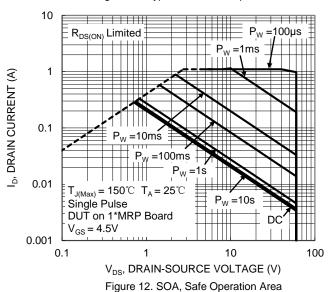


Figure 10. Typical Junction Capacitance



March 2020

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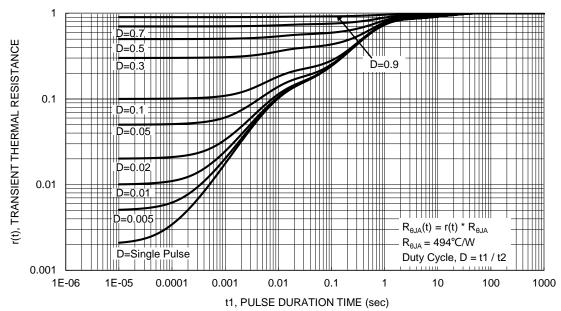


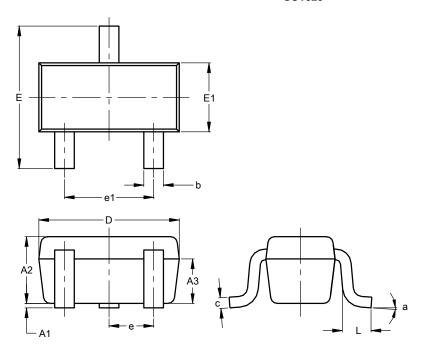
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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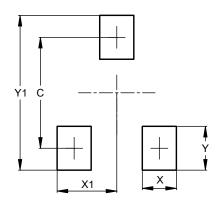


SOT523						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.60	0.80	0.75			
A3	0.45	0.65	0.50			
b	0.15	0.30	0.22			
С	0.10	0.20	0.12			
D	1.50	1.70	1.60			
Е	1.45	1.75	1.60			
E1	0.75	0.85	0.80			
е	0.50 BSC					
e1	0.90	1.10	1.00			
ш	0.20	0.40	0.33			
а	0°		8°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
С	1.29
Х	0.40
X1	0.70
Υ	0.51
Y1	1.80



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